

## 製品概要

## NSBA115TDP6: Dual PNP Bipolar Digital Transistor (BRT)

技術情報は、データシートをご参照ください。

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

## 特長

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

## 電氣的仕様

| 製品             | Compliance             | Status | Polarity | $I_C$ Continuous (A) | $V_{BRICE0}$ Min (V) | $h_{FE}$ Min | R1 (k $\Omega$ ) | R2 (k $\Omega$ ) | R1/R2 Typ | $V_{i(off)}$ Max (V) | $V_{i(on)}$ Min (V) | Package Type |
|----------------|------------------------|--------|----------|----------------------|----------------------|--------------|------------------|------------------|-----------|----------------------|---------------------|--------------|
| NSBA115TDP6T5G | Pb-free<br>Halide free | Active | Dual PNP | 0.1                  | 50                   | 160          | 100              | Infinity         | -         | 0.5                  | 1.5                 | SOT-963      |

詳細は、弊社 [www.onsemi.jp](http://www.onsemi.jp) の営業または販売代理店にお問い合わせください。

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